

The listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (Original) A method of manufacturing a semiconductor device comprising the steps of:

emitting a laser beam which is a fundamental wave from a laser oscillator;
delivering the laser beam onto a semiconductor; and
crystallizing the semiconductor by irradiating with the laser beam which generates multiphoton absorption while moving the surface of the semiconductor relatively to the laser beam.

2. (Original) A method of manufacturing a semiconductor device comprising the steps of:

forming an impurity region in a semiconductor;
emitting a laser beam which is a fundamental wave from a laser oscillator;
delivering the laser beam onto the semiconductor; and
activating the impurity region by irradiating with the laser beam which generates multiphoton absorption while moving the surface of the semiconductor relatively to the laser beam.

3. (Original) A method of manufacturing a semiconductor device comprising the steps of:

emitting a laser beam which is a fundamental wave from a laser oscillator;
delivering the laser beam onto a semiconductor; and
crystallizing the semiconductor by irradiating with the laser beam which generates multiphoton absorption while moving the surface of the semiconductor relatively to the laser beam,

wherein the laser beam has a peak out power ranging from 1 GW/cm² to 1 TW/cm².

4. (Original) A method of manufacturing a semiconductor device comprising the steps of:

forming an impurity region in a semiconductor;
emitting a laser beam which is a fundamental wave from a laser oscillator;
delivering the laser beam onto the semiconductor; and
activating the impurity region by irradiating with the laser beam which generates multiphoton absorption while moving the surface of the semiconductor relatively to the laser beam,

wherein the laser beam has a peak out power ranging from 1 GW/cm² to 1 TW/cm².

5. (Original) A method of manufacturing a semiconductor device comprising the steps of:

forming a semiconductor layer over a substrate;
forming an insulating layer adjacent to the semiconductor layer;
forming a conductive layer adjacent to the insulating layer;
emitting a laser beam which is a fundamental wave from a laser oscillator;
delivering the laser beam onto the semiconductor layer; and
crystallizing the semiconductor layer by irradiating with the laser beam which generates multiphoton absorption while moving the surface of the semiconductor layer relatively to the laser beam.

6. (Currently amended) The method of manufacturing the semiconductor device according to ~~any one of claims~~ claim 1 to 5,

wherein the laser beam which is a fundamental wave is oscillated with a pulse width of [[a]] 1 femtosecond or more and 10 picoseconds or less.

7. (Currently amended) The method of manufacturing the semiconductor device according to ~~any one of claims~~ claim 1 to 5,
wherein the laser beam has a repetition rate of 10MHz or more.

8. (Currently amended) The method of manufacturing the semiconductor device according to ~~any one of claims~~ claim 1 to 5,

wherein the laser beam which is a fundamental wave is emitted from a laser oscillator which includes a crystal selected from the group consisting of Sapphire, YAG, ceramics YAG, ceramics Y_2O_3 , KGW, KYW, Mg_2SiO_4 , YLF, YVO_4 , and $GdVO_4$,

wherein ~~the crystal is added at least one of Nd, Yb, Cr, Ti, Ho, and Er~~ is added to the crystal as a dopant.

9. (Currently amended) The method of manufacturing the semiconductor device according to ~~any one of claims~~ claim 1 to 5,

wherein the laser beam has one of a linear shape and an elliptical shape on the irradiation surface.

10. (Original) A laser irradiation method comprising the steps of:
emitting a first laser beam which is a fundamental wave from a laser oscillator;
processing the first laser beam into a second laser beam which has one of a linear shape and a rectangular shape on an irradiation surface;
irradiating an object with the second laser beam which generates a multiphoton absorption.

11. (Original) The laser irradiation method according to claim 10, wherein the first laser beam has a repetition rate of 10 MHz or higher.

12. (Currently Amended) The laser irradiation method according to claim 10, wherein the first laser beam which is a fundamental wave is oscillated with a pulse width of [[a]] 1 femtosecond or more and 10 picoseconds or less.

13. (Original) The laser irradiation method according to claim 10, wherein the first laser beam is a laser beam emitted from a laser oscillator which includes a crystal selected from the group consisting of Sapphire, YAG, ceramics YAG, ceramics Y_2O_3 , KGW, KYW, Mg_2SiO_4 , YLF, YVO_4 , and $GdVO_4$, wherein ~~the crystal is added~~ at least one of Nd, Yb, Cr, Ti, Ho, and Er is added to the crystal as a dopant.

14. (Original) A laser irradiation apparatus comprising:
a solid state laser oscillator for emitting a laser beam which is a fundamental wave;
a mechanism for projecting and delivering the laser beam which is the fundamental wave onto an irradiation surface, said mechanism including a condenser lens; and
means for moving the irradiation surface relatively to the laser beam which is the fundamental wave,
wherein the condenser lens forms the laser beam which is the fundamental wave into one of a linear shape and an elliptical shape.

15. (Currently amended) The laser irradiation apparatus according to claim [[15]] 14, wherein the condenser lens includes two pieces of convex cylindrical lenses.

16. (Currently amended) The laser irradiation method apparatus according to claim [[15]] 14, wherein the laser beam has a repetition rate of 10 MHz or higher.

17. (Currently amended) The laser irradiation apparatus according to claim [[15]] 14, wherein the laser beam emitted from the laser oscillator is oscillated with a pulse width of 1 femtosecond or more and 10 picoseconds or less.

18. (Currently amended) The laser irradiation apparatus according to claim [[15]] 14, wherein the laser beam oscillated from the laser oscillator is emitted from a laser oscillator which includes a crystal selected from the group consisting of Sapphire, YAG, ceramics YAG, ceramics Y_2O_3 , KGW, KYW, Mg_2SiO_4 , YLF, YVO_4 , and $GdVO_4$ added at least one of Nd, Yb, Cr, Ti, Ho, and Er as a dopant.

19. (Currently amended) The laser irradiation apparatus according to claim [[15]] 14, wherein the laser beam has a peak out power ranging from 1 GW/cm^2 to 1 TW/cm^2 .

20. (New) The method of manufacturing the semiconductor device according to claim 2,

wherein the laser beam which is a fundamental wave is oscillated with a pulse width of 1 femtosecond or more and 10 picoseconds or less.

21. (New) The method of manufacturing the semiconductor device according to claim 3,

wherein the laser beam which is a fundamental wave is oscillated with a pulse width of 1 femtosecond or more and 10 picoseconds or less.

22. (New) The method of manufacturing the semiconductor device according to claim 4,

wherein the laser beam which is a fundamental wave is oscillated with a pulse width of 1 femtosecond or more and 10 picoseconds or less.

23. (New) The method of manufacturing the semiconductor device according to claim 5,

wherein the laser beam which is a fundamental wave is oscillated with a pulse width of 1 femtosecond or more and 10 picoseconds or less.

24. (New) The method of manufacturing the semiconductor device according to claim 2,

wherein the laser beam has a repetition rate of 10MHz or more.

25. (New) The method of manufacturing the semiconductor device according to claim 3,

wherein the laser beam has a repetition rate of 10MHz or more.

26. (New) The method of manufacturing the semiconductor device according to claim 4,

wherein the laser beam has a repetition rate of 10MHz or more.

27. (New) The method of manufacturing the semiconductor device according to claim 5,

wherein the laser beam has a repetition rate of 10MHz or more.

28. (New) The method of manufacturing the semiconductor device according to claim 2,

wherein the laser beam which is a fundamental wave is emitted from a laser oscillator which includes a crystal selected from the group consisting of Sapphire, YAG, ceramics YAG, ceramics Y_2O_3 , KGW, KYW, Mg_2SiO_4 , YLF, YVO_4 , and $GdVO_4$,

wherein at least one of Nd, Yb, Cr, Ti, Ho, and Er is added to the crystal as a dopant.

29. (New) The method of manufacturing the semiconductor device according to claim 3,

wherein the laser beam which is a fundamental wave is emitted from a laser oscillator which includes a crystal selected from the group consisting of Sapphire, YAG, ceramics YAG, ceramics Y_2O_3 , KGW, KYW, Mg_2SiO_4 , YLF, YVO_4 , and $GdVO_4$,

wherein at least one of Nd, Yb, Cr, Ti, Ho, and Er is added to the crystal as a dopant.

30. (New) The method of manufacturing the semiconductor device according to claim 4,

wherein the laser beam which is a fundamental wave is emitted from a laser oscillator which includes a crystal selected from the group consisting of Sapphire, YAG, ceramics YAG, ceramics Y_2O_3 , KGW, KYW, Mg_2SiO_4 , YLF, YVO_4 , and $GdVO_4$,

wherein at least one of Nd, Yb, Cr, Ti, Ho, and Er is added to the crystal as a dopant.

31. (New) The method of manufacturing the semiconductor device according to claim 5,

wherein the laser beam which is a fundamental wave is emitted from a laser oscillator which includes a crystal selected from the group consisting of Sapphire, YAG, ceramics YAG, ceramics Y_2O_3 , KGW, KYW, Mg_2SiO_4 , YLF, YVO_4 , and $GdVO_4$,

wherein at least one of Nd, Yb, Cr, Ti, Ho, and Er is added to the crystal as a dopant.

32. (New) The method of manufacturing the semiconductor device according to claim 2,

wherein the laser beam has one of a linear shape and an elliptical shape on the irradiation surface.

33. (New) The method of manufacturing the semiconductor device according to claim 3,

wherein the laser beam has one of a linear shape and an elliptical shape on the irradiation surface.

34. (New) The method of manufacturing the semiconductor device according to claim 4,

wherein the laser beam has one of a linear shape and an elliptical shape on the irradiation surface.

35. (New) The method of manufacturing the semiconductor device according to claim 5,

wherein the laser beam has one of a linear shape and an elliptical shape on the irradiation surface.